

General purpose transistor

QSZ2

A 2SB1695 and a 2SD2657 are housed independently in a TSMT5 package.

●Structure

Silicon epitaxial planar transistor

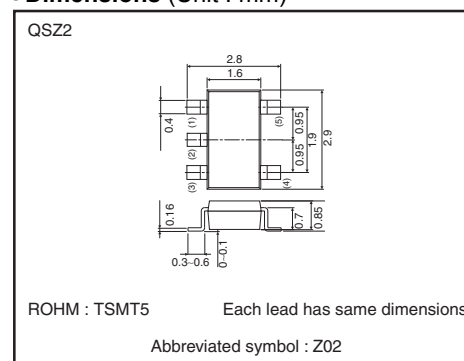
●Features

- 1) Low $V_{CE(sat)}$
- 2) Small package

●Applications

DC / DC converter
 Motor driver

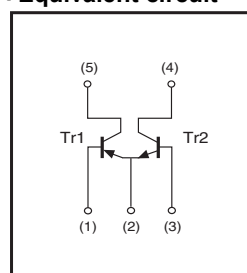
●Dimensions (Unit : mm)



●Packaging specifications

Type	QSZ2
Package	TSMT5
Marking	Z02
Code	TR
Basic ordering unit(pieces)	3000

●Equivalent circuit



●Absolute maximum ratings ($T_a=25^{\circ}\text{C}$)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	-30	V
Collector-emitter voltage	V_{CEO}	-30	V
Emitter-base voltage	V_{EBO}	-6	V
Collector current	I_C	-1.5	A
	I_{CP}	-3	A *1
Collector power dissipation	P_C	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T_J	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

*1 Single pulse $P_w=1\text{ms}$.

*2 Each terminal mounted on a recommended land.

*3 Mounted on a $25\text{mm} \times 25\text{mm} \times 0.8\text{mm}$ ceramic substrate.

Tr2

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	1.5	A
	I_{CP}	3	A *1
Power dissipation	P_C	500	mW/Total *2
		1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	T_J	150	$^{\circ}\text{C}$
Range of storage temperature	T_{stg}	-55 to +150	$^{\circ}\text{C}$

*1 Single pulse $P_w=1\text{ms}$.

*2 Each terminal mounted on a recommended land.

*3 Mounted on a $25\text{mm} \times 25\text{mm} \times 0.8\text{mm}$ ceramic substrate.

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	-30	-	-	V	I _C =-10μA
Collector-emitter breakdown voltage	BV _{CEO}	-30	-	-	V	I _C =-1mA
Emitter-base breakdown voltage	BV _{EBO}	-6	-	-	V	I _E =-10μA
Collector cutoff current	I _{CBO}	-	-	-100	nA	V _{CB} =-30V
Emitter cutoff current	I _{EBO}	-	-	-100	nA	V _{EB} =-6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-200	-370	mV	I _C =-1mA, I _B =-50mA
DC current transfer ratio	h _{FE}	270	-	680	-	V _{CE} =-2V, I _C =-100mA*
Transition frequency	f _T	-	280	-	MHz	V _{CE} =-2V, I _E =100mA, f=100MHz*
Output capacitance	C _{ob}	-	13	-	pF	V _{CB} =-10V, I _E =0mA, f=1MHz

* Pulsed

Tr2

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CBO}	30	-	-	V	I _C =10μA
Collector-emitter breakdown voltage	BV _{CEO}	30	-	-	V	I _C =1mA
Emitter-base breakdown voltage	BV _{EBO}	6	-	-	V	I _E =10μA
Collector cutoff current	I _{CBO}	-	-	100	nA	V _{CB} =30V
Emitter cutoff current	I _{EBO}	-	-	100	nA	V _{EB} =6V
Collector-emitter saturation voltage	V _{CE(sat)}	-	140	350	mV	I _C =1A, I _B =50mA
DC current gain	h _{FE}	270	-	680	-	V _{CE} =2V, I _C =100mA*
Transition frequency	f _T	-	300	-	MHz	V _{CE} =2V, I _E =-100mA, f=100MHz*
Corrector output capacitance	C _{ob}	-	11	-	pF	V _{CB} =10V, I _E =0A, f=1MHz

* Pulsed

●Electrical characteristic curves

Tr1

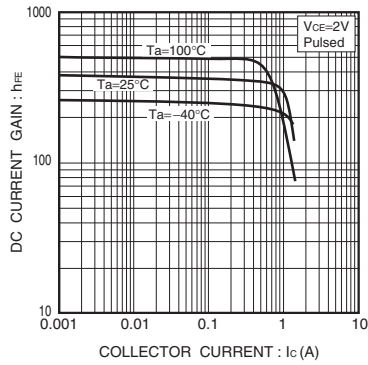


Fig.1 DC current gain vs. collector current

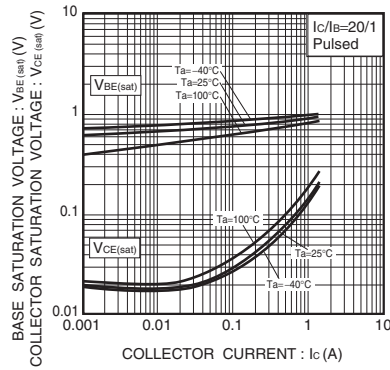


Fig.2 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

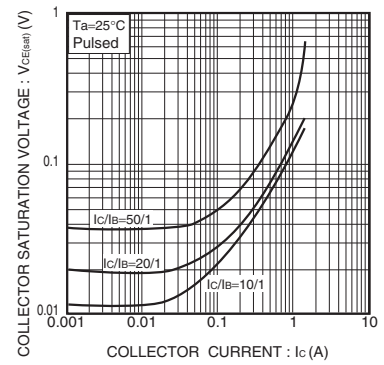


Fig.3 Collector-emitter saturation voltage vs. collector current

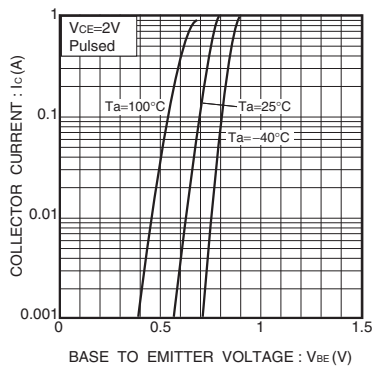


Fig.4 Grounded emitter propagation characteristics

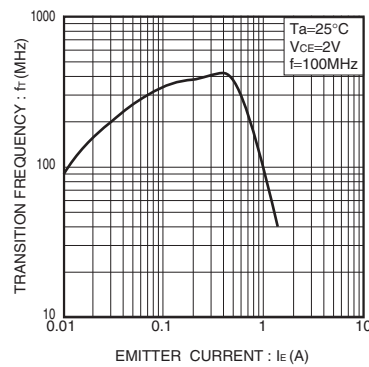


Fig.5 Gain bandwidth product vs. emitter current

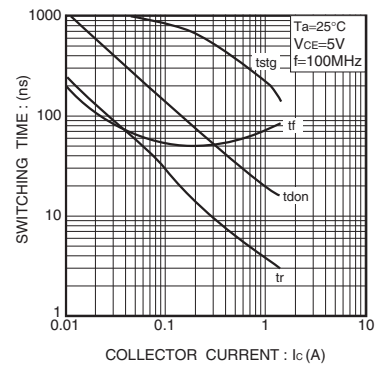


Fig.6 Switching time

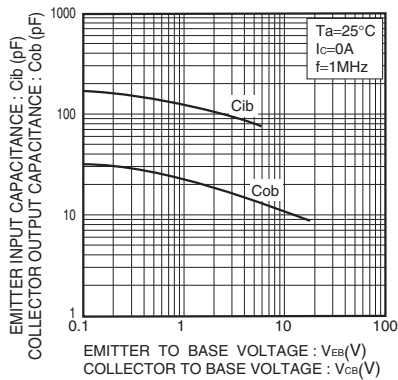


Fig.7 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Tr2

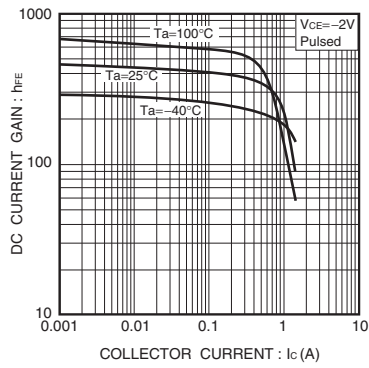


Fig.8 DC current gain vs. collector current

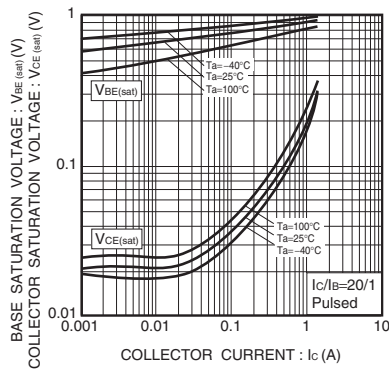


Fig.9 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

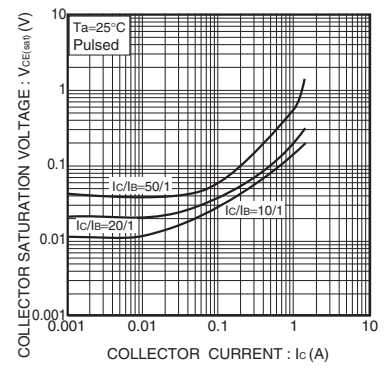


Fig.10 Collector-emitter saturation voltage vs. collector current

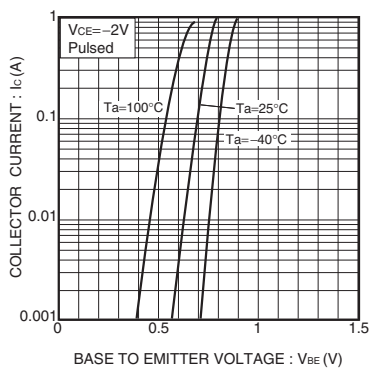


Fig.11 Grounded emitter propagation characteristics

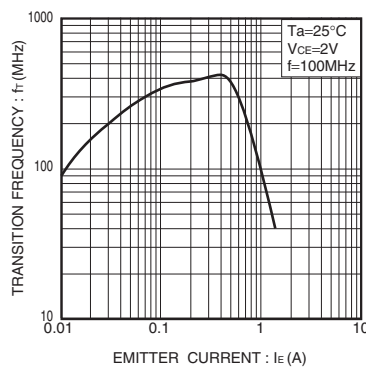


Fig.12 Gain bandwidth product vs. emitter current

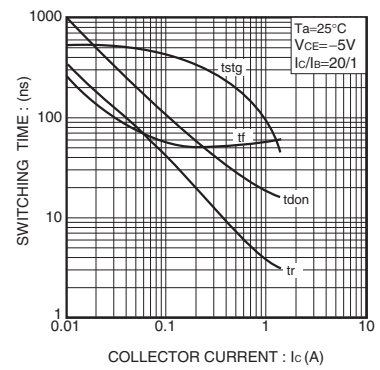


Fig.13 Switching time

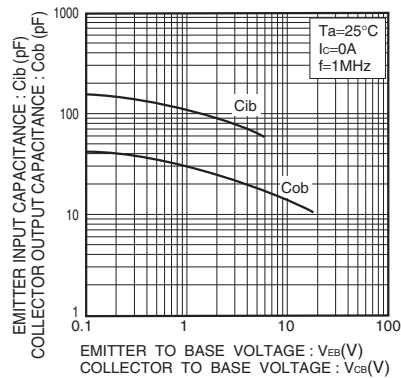


Fig.14 Collector output capacitance vs. collector-base voltage
Emitter input capacitance vs. emitter-base voltage

Notes

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